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Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (Currently Amended): A method of forming a pattern on a semiconductor wafer, the method comprising:

modulating light directed to a first portion of a photosensitive layer using a plurality of tilted mirrors in a mirror array; and

modulating light directed to a second portion of a photosensitive layer using a plurality of piston mirrors in the mirror array, the plurality of piston mirrors configured such that the displacement of the mirrors from a neutral plane of the mirror array creates varying degrees of interference of light waves on the image, the amount of interference corresponding to the degree of displacement, wherein tilting and piston displacement modes are simultaneously performed on an individual mirror in the array.

2 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the tilted mirrors are controlled such that at least two adjacent mirrors generate a phase difference of about 520 degrees on a predetermined portion of the photosensitive layer.

3-4. (Cancelled).

5 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the piston mode is selected to mimic the functioning of resolution enhancement features.

6 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the individual mirrors having dual tilting and piston displacement modes are used to write a first feature of the pattern and wherein at least one of tilted mirrors and piston mirrors are used to write a second feature of the pattern.

7 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the piston mirrors are configured such that two adjacent mirrors exhibit about 180 degrees in phase difference.

8 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the tilted mirrors are controlled such that at least two adjacent mirrors generate a phase difference in the range from about 400 to 600 degrees on a predetermined portion of the photosensitive layer.

9 (Original): The method of forming a pattern on a semiconductor wafer as recited in claim 1, wherein the piston mirrors are configured such that two adjacent mirrors exhibit a phase difference of about 280 degrees.

10-12 (Cancelled).

13 (Currently Amended): A method of forming a pattern on a reticle substrate, the method comprising:

modulating light directed to a first portion of a photosensitive layer using a plurality of tilted mirrors in a mirror array wherein each of the tilted mirrors are included as part of a piston displacement element so that the combination of tilting of the mirrors and the relative displacement of the mirrors combine to create varying degrees of interference of light waves on the image, the amount of interference corresponding to a combination of the degree of tilting and the degree of displacement; and

modulating light directed to a second portion of a photosensitive layer using a plurality of tilted mirrors in a mirror array wherein each of the tilted mirrors are included as part of a piston displacement element so that the combination of tilting of the mirrors and the relative displacement of the mirrors combine to create mirrors in the mirror array, the plurality of piston mirrors configured such that the displacement of the mirrors from a neutral plane of the mirror array creates varying degrees of interference of light waves on the image, the amount of interference corresponding to a combination of the degree of tilting and the degree of displacement.

14 (Currently Amended): The method of forming a pattern on a recticle substrate as recited in claim 13, wherein the ~~tilted~~-mirrors are controlled such that at least two adjacent mirrors generate a phase difference of about 520 degrees on a predetermined portion of the photosensitive layer.

15-16 (Cancelled).

17 (Currently Amended): The method of forming a pattern on a recticle substrate as recited in claim 13, wherein the individual mirrors ~~having dual tilting and piston displacement modes~~ are used to write a first feature of the pattern and wherein at least one of ~~the tilted mirrors and piston~~ mirrors are used to write a second feature of the pattern.

18 (Currently Amended): The method of forming a pattern on a recticle substrate as recited in claim 13, wherein [[the]] a piston component of the mirrors [[are]] is configured such that two adjacent mirrors exhibit about 180 degrees in phase difference.

19 (Original): The method of forming a pattern on a recticle substrate as recited in claim 1, wherein the piston mirrors are configured such that two adjacent mirrors exhibit a phase difference of about 280 degrees.

20 (Cancelled).